

N-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
12	0.003 at V _{GS} = 4.5 V	25
	0.004 at V _{GS} = 2.5 V	22
	0.005 at V _{GS} = 1.8 V	19

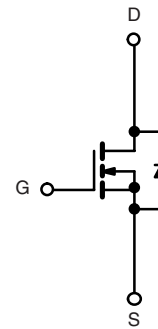
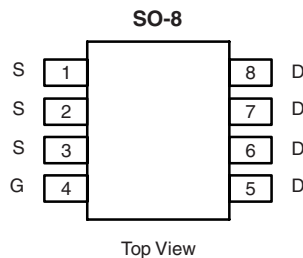
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET
- PWM Optimized
- 100 % R_g Tested



APPLICATIONS

- Low Voltage Synchronous Rectification
- Low Voltage LDO Pass Transistor



Ordering Information: Si4836DY-T1-E3 (Lead (Pb)-free)
Si4836DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V _{DS}	12		V
Gate-Source Voltage	V _{GS}	± 8		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	25	17	A
	T _A = 70 °C	20	13	
Pulsed Drain Current (10 μs Pulse Width)	I _{DM}	60		
Continuous Source Current (Diode Conduction) ^a	I _S	2.9	1.3	
Maximum Power Dissipation ^a	T _A = 25 °C	3.5	1.6	W
	T _A = 70 °C	2.2	1	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 s	29	35	°C/W
	Steady State	67	80	
Maximum Junction-to-Foot (Drain)	R _{thJF}	13	16	

Notes:
a. Surface Mounted on 1" x 1" FR4 board.

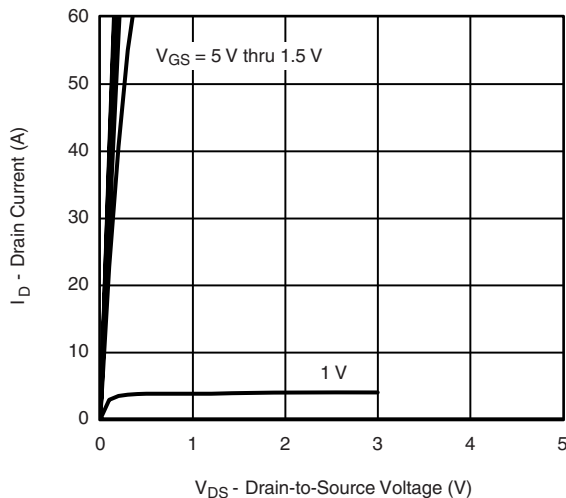
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.40			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 8\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 9.6\ \text{V}, V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 9.6\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}, V_{GS} = 4.5\ \text{V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5\ \text{V}, I_D = 25\ \text{A}$		0.0025	0.003	Ω
		$V_{GS} = 2.5\ \text{V}, I_D = 22\ \text{A}$		0.0031	0.004	
		$V_{GS} = 1.8\ \text{V}, I_D = 19\ \text{A}$		0.004	0.005	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 6\ \text{V}, I_D = 25\ \text{A}$		80		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.9\ \text{A}, V_{GS} = 0\ \text{V}$		0.56	1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 6\ \text{V}, V_{GS} = 4.5\ \text{V}, I_D = 25\ \text{A}$		51	75	nC
Gate-Source Charge	Q_{gs}			6.6		
Gate-Drain Charge	Q_{gd}			9.1		
Gate Resistance	R_g		1.0	1.6	2.7	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 6\ \text{V}, R_L = 6\ \Omega$ $I_D \cong 1\ \text{A}, V_{GEN} = 4.5\ \text{V}, R_g = 6\ \Omega$		35	55	ns
Rise Time	t_r			41	65	
Turn-Off Delay Time	$t_{d(off)}$			190	290	
Fall Time	t_f			115	175	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.9\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		60	90	

Notes:

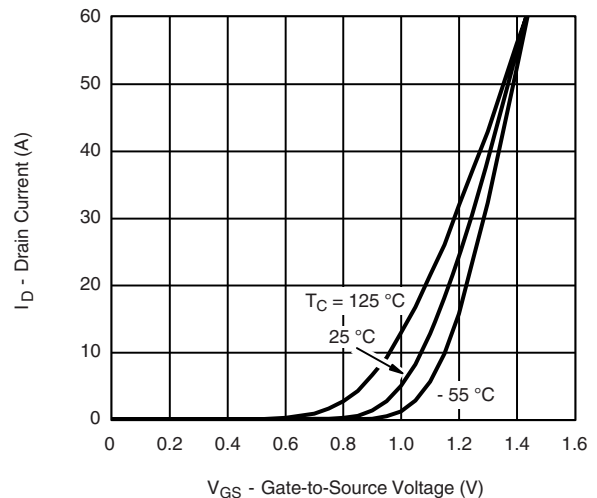
- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted

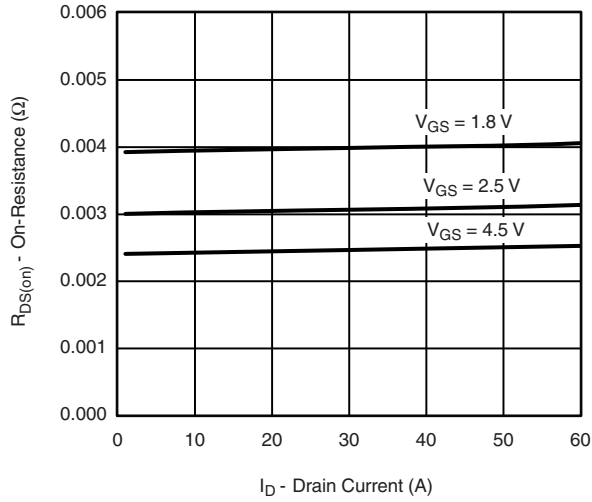


Output Characteristics

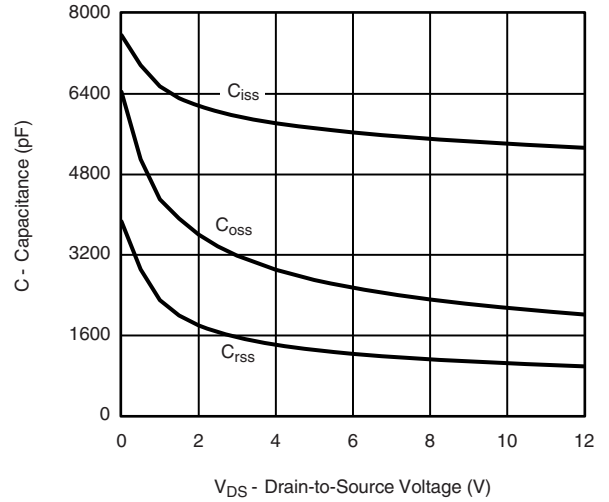


Transfer Characteristics

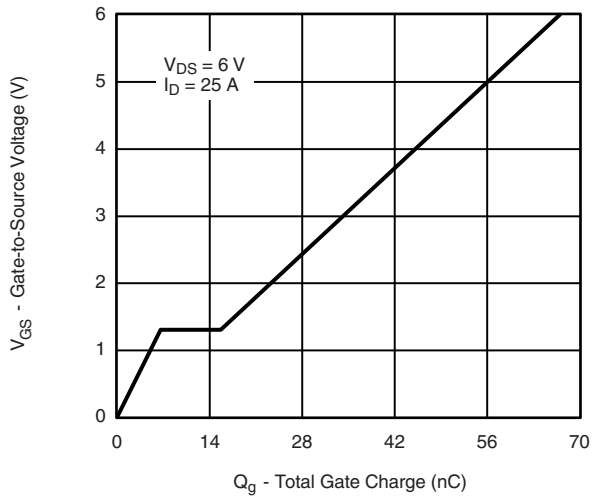
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



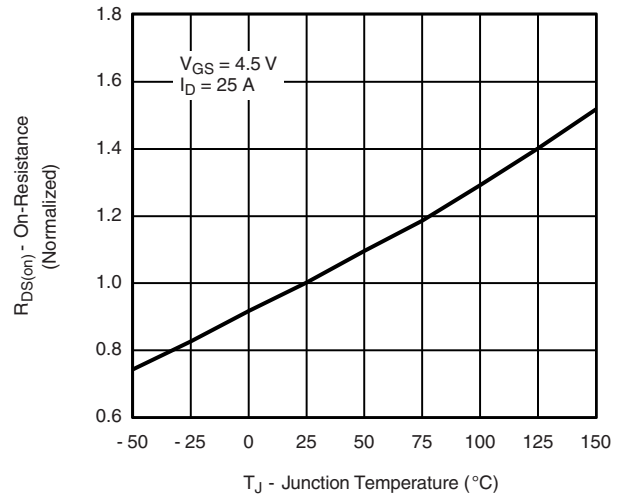
On-Resistance vs. Drain Current



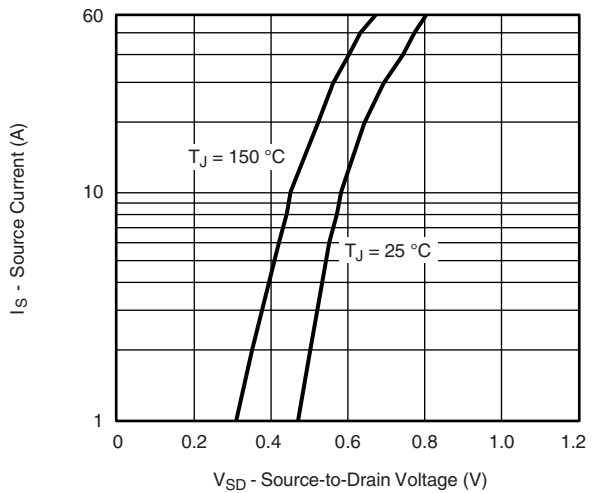
Capacitance



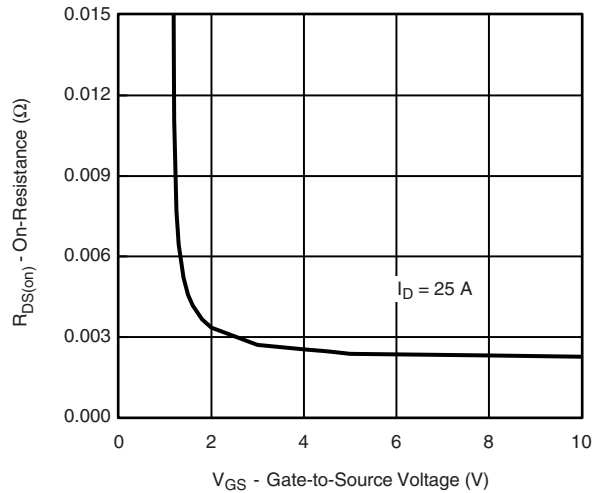
Gate Charge



On-Resistance vs. Junction Temperature

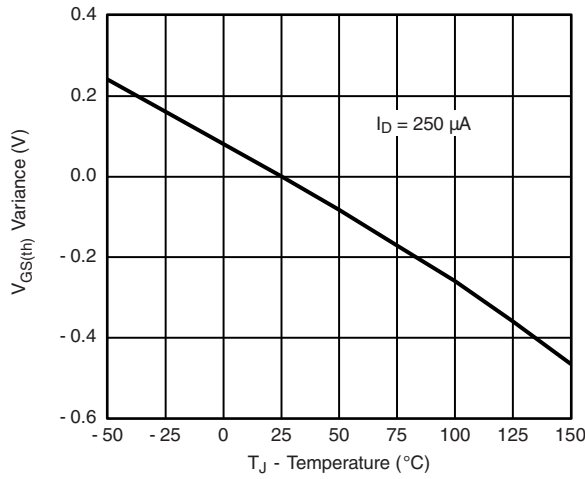


Source-Drain Diode Forward Voltage

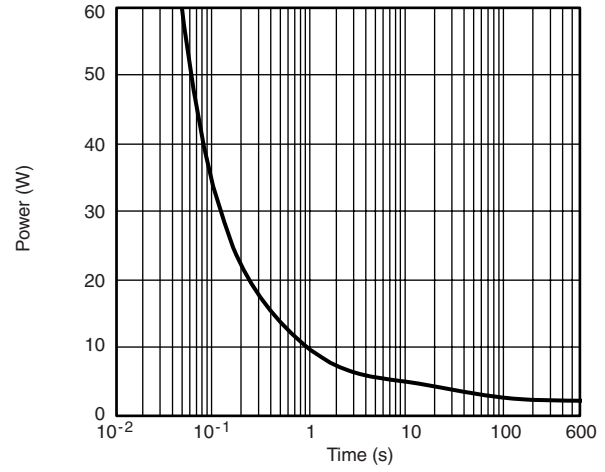


On-Resistance vs. Gate-to-Source Voltage

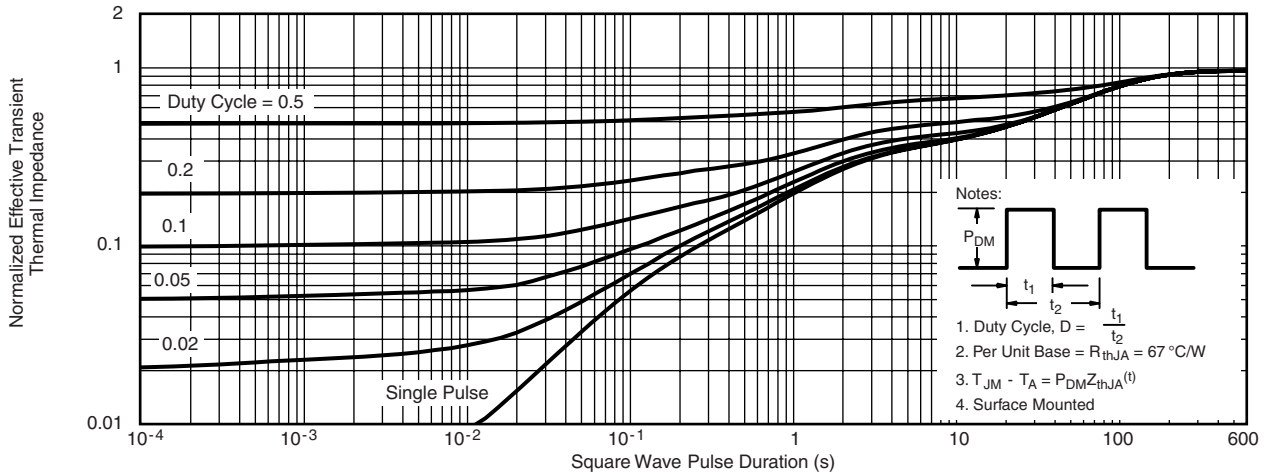
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



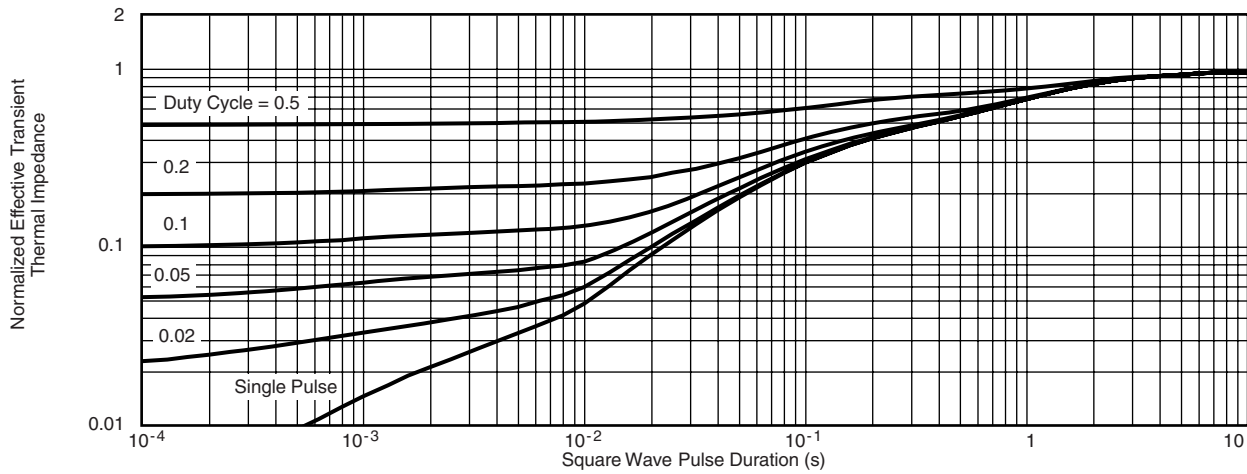
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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